

B<sup>1</sup>  
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C1

1. (Amended) A method for manufacturing a semiconductor device comprising the steps of:  
forming a semiconductor film comprising amorphous silicon over a substrate;  
crystallizing said semiconductor film by irradiating a laser light; forming an insulating film on the crystallized semiconductor film by a vapor phase deposition; and  
irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas.

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2. (Amended) The method of claim 1 wherein said intense light is an IR light.

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3. (Amended) The method of claim 1 wherein said vapor phase deposition is performed by a plasma CVD or a low pressured CVD.

4. (Amended) The method of claim 1 wherein the irradiation of said intense light is performed in order to reduce an interfacial layer density to  $10^{11} \text{ cm}^{-2}$  or lower.

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6. (Amended) A method for manufacturing a semiconductor device comprising the steps of:  
forming a semiconductor film comprising amorphous silicon over a substrate;  
crystallizing said semiconductor film by irradiating a laser light;  
forming an insulating film comprising silicon oxide on the crystallized semiconductor film by a vapor phase deposition; and

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas.

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7. (Amended) The method of claim 6 wherein said intense light is an IR light.

8. (Amended) The method of claim 6 wherein said vapor phase deposition is performed by a plasma CVD or a low pressured CVD.

9. (Amended) The method of claim 6 wherein the irradiation of said intense light is performed in order to reduce an interfacial layer density to  $10^{11} \text{ cm}^{-2}$  or lower.

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11. (Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate;

crystallizing said semiconductor film by irradiating a laser light;

forming an insulating film comprising silicon oxide on the crystallized semiconductor film by a vapor phase deposition using TEOS; and

irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas.

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12. (Amended) The method of claim 11 wherein said intense light is an IR light.

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13.

(Amended) The method of claim 11 wherein said vapor phase deposition is performed by a plasma CVD or a low pressured CVD.

Please add new claims 29-37 as follows:

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--29. The method of claim 11 wherein said the irradiation of said intense light is performed in order to reduce an interfacial layer density to  $10^{11} \text{ cm}^{-2}$  or lower.

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30. A method for manufacturing a semiconductor device comprising the steps of:  
forming a crystalline semiconductor film over a substrate;  
forming an insulating film comprising silicon oxide on said crystalline semiconductor film by a vapor phase deposition; and  
irradiating an intense light to said insulating film in an atmosphere comprising an oxygen gas.

31. The method of claim 30 wherein said intense light is an IR light.

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32. The method of claim 30 wherein said vapor phase deposition is performed by a plasma CVD or a low pressured CVD.

33. The method of claim 30 wherein the irradiation of said intense light is performed in order to reduce an interfacial layer density to  $10^{11} \text{ cm}^{-2}$  or lower.

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34. A method for manufacturing a semiconductor device comprising the steps of:  
forming a crystalline semiconductor film over a substrate;